

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for forming a contact for a semiconductor device, comprising:

forming an interlayer dielectric over the semiconductor device;

depositing a polysilicon material over the semiconductor device, wherein the depositing a polysilicon material includes:

depositing the polysilicon material over the interlayer dielectric;

oxidizing at least a portion of the polysilicon material to form an oxide;

etching at least one of the oxide and the polysilicon material to form a contact hole,

wherein the etching at least one of the oxide and the polysilicon material includes:

etching the polysilicon material using the oxide as a mask, the etching of the

polysilicon material removing at least some of the oxide; and

filling the contact hole to form the contact for the semiconductor device

2. (Canceled)

3. (Canceled)

4. (Currently amended) The method of claim [[3]] 1, wherein the etching at least one

of the oxide and the polysilicon material further includes:

etching the interlayer dielectric using the polysilicon material as a mask to form the contact hole, the contact hole extending through the interlayer dielectric.

5. (Original) The method of claim 1, further comprising:

forming an antireflective coating on the polysilicon material;

forming and patterning a photoresist on the antireflective coating; and

etching the antireflective coating not located under the photoresist.

6. (Original) The method of claim 5, further comprising:

stripping the photoresist prior to oxidizing the polysilicon material.

7. (Original) The method of claim 1, wherein the filling the contact hole includes:

forming a barrier layer on surfaces of the contact hole, and

depositing tungsten to at least partially fill the contact hole.

8. (Original) The method of claim 1, further comprising:

polishing the semiconductor device to remove the polysilicon material after etching the at least one of the oxide and the polysilicon material.

9-30 (Canceled)

31. (New) A method for forming a contact for a semiconductor device, comprising:
depositing a polysilicon material over the semiconductor device;
oxidizing at least a portion of the polysilicon material to form an oxide;
etching at least one of the oxide and the polysilicon material to form a contact hole; and
filling the contact hole to form the contact for the semiconductor device, wherein the
filling the contact hole includes:

forming a barrier layer on surfaces of the contact hole, and
depositing tungsten to at least partially fill the contact hole.

32. (New) The method of claim 31, further comprising:
forming an interlayer dielectric over the semiconductor device; and
wherein the depositing a polysilicon material includes:
depositing the polysilicon material over the interlayer dielectric.

33. (New) The method of claim 32, wherein the etching at least one of the oxide and
the polysilicon material includes:

etching the polysilicon material using the oxide as a mask, the etching of the polysilicon
material removing at least some of the oxide.

34. (New) The method of claim 33, wherein the etching at least one of the oxide and
the polysilicon material further includes:

etching the interlayer dielectric using the polysilicon material as a mask to form the contact hole, the contact hole extending through the interlayer dielectric.

35. (New) The method of claim 31, further comprising:
forming an antireflective coating on the polysilicon material;
forming and patterning a photoresist on the antireflective coating; and
etching the antireflective coating not located under the photoresist.
36. (New) The method of claim 35, further comprising:
stripping the photoresist prior to oxidizing the polysilicon material.
37. (New) The method of claim 31, further comprising:
polishing the semiconductor device to remove the polysilicon material after etching the at least one of the oxide and the polysilicon material.
38. (New) A method of forming a contact hole through an inter-layer dielectric, comprising:
forming a layer of polysilicon material over the inter-layer dielectric;

forming an anti-reflective coating (ARC) layer on the layer of polysilicon material in a pattern corresponding to a desired shape of the contact hole;

oxidizing the layer of polysilicon material around the pattern of the ARC layer to form an oxidized layer;

removing the ARC layer to expose an un-oxidized portion of the polysilicon layer beneath the oxidized layer having a shape corresponding to the pattern;

etching the un-oxidized portion of the polysilicon layer to form a first contact hole through the un-oxidized portion of the polysilicon layer; and

etching the inter-layer dielectric through the first contact hole using the polysilicon layer as a mask to form a second contact hole through the inter-layer dielectric.